Reliable High-Performance Gate Oxides for Wide Band Gap Devices

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Impact
- Increased System Performance and Reliability
- Reduced System Cost
- Reduced Power Electronics Size

Purpose
- Gate dielectrics are a key limiter in GaN- and SiC-based power electronics technology
- Engineered gates will enable the development of robust and reliable MOSFETs

Funded by the U.S. DOE Energy Storage Systems Program through Sandia National Laboratories. Sandia National Laboratories is a multi-program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy’s National Nuclear Security Administration under contract DE-AC04-94AL85000. SAND2014-17652PE